

FORM 1449*

INFORMATION DISCLOSURE STATEMENT

IN AN APPLICATION

(Use several sheets if necessary)

Docket Number:

10233.81USW1

Application Number:

09/208,105

Applicant: SAKAMOTO

Filing Date: November 25,
1998

Group Art Unit: 2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
ON	4,134,778	January, 1979	Sheng, et al.			
ON	4,682,195	July, 1987	Yilmaz			
ON	5,025,293	June, 1991	Seki			
ON	5,169,793	December, 1992	Okabe, et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
ON	54-53873	April, 1979	Japan				
	62-54961	March, 1987	Japan				
	0 213 972	March, 1987	EPO				
	62-298120	December, 1987	Japan			Abstract	
	64-19771	January, 1989	Japan			Abstract	
	1-287965	November, 1989	Japan			Abstract	
	2-196471	August, 1990	Japan				
	3-259537	November, 1991	Japan			Abstract	
	4-229661	August, 1992	Japan				
	2526653	June, 1996	Japan				
ON	2858404	December, 1998	Japan				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

ON	Esaki, et al., "A 900 MHz 100 W VD-Mosfet with Silicide Gate Self-aligned Channel", International Electron Devices Meeting. Technical Digest, December 1984, pages 447-450
ON	Akiyama, et al., "Partial Lifetime Control in IGBT by Helium Irradiation Through Mask Patterns", Power Semiconductor Devices and ICS, 1991. International Symposium on Baltimore, MD, USA 22-24 April 1991, New York, NY, USA, IEEE, US, April 22, 1991, pages 187-191

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PATENT TRADEMARK OFFICE

EXAMINER

ON

DATE CONSIDERED

12/11/04

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.